PROCESS CPD82X

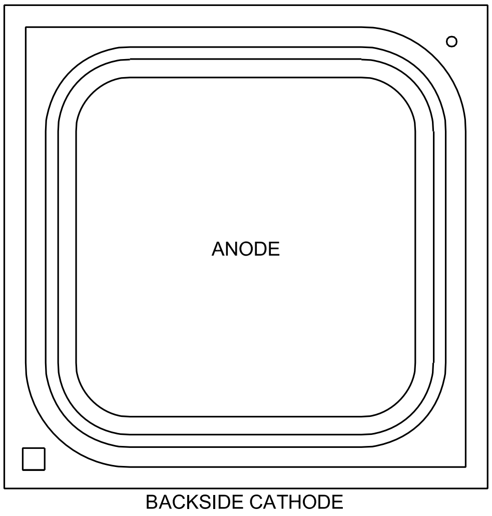
Schottky Diode

High Current, Low V_F Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.6 x 14.6 MILS
Die Thickness	5.5 MILS
Anode Bonding pad Area	11.8 x 11.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



R0

GROSS DIE PER 5 INCH WAFER

80,282

PRINCIPAL DEVICE TYPES

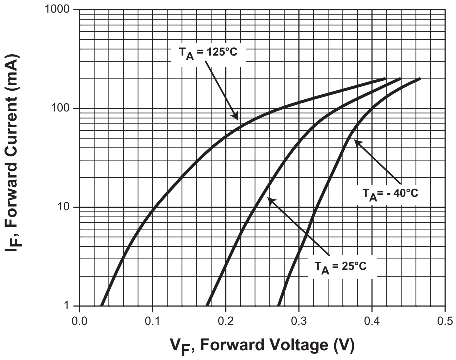
CMDSH2-3
CMDSH2-4L
CMOSH2-4L
CMUSH2-4L
CMKSH2-4L
CMXSH2-4L

R2 (22-March 2010)

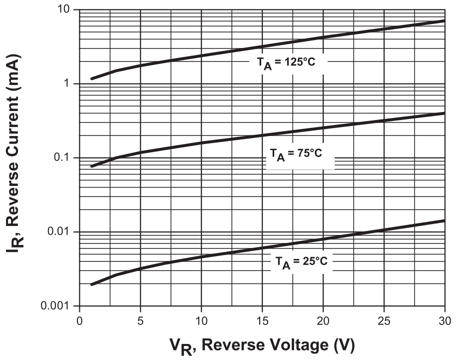
PROCESS CPD82X

Typical Electrical Characteristics

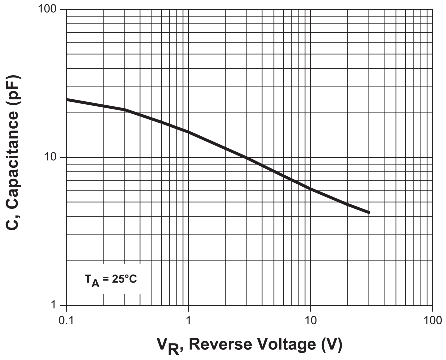
Forward Voltage



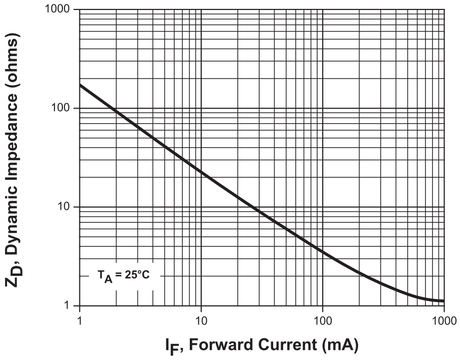
Leakage Current



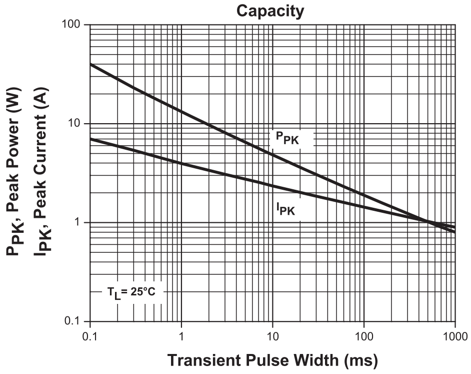
Capacitance



Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating